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# Wide-Bandgap Semiconductor Materials and Devices 11 -and- State-of-the-Art Program on Compound Semiconductors 52 (SOTAPOCS 52)

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## Table of Contents

*Preface* *iii*

### Chapter 1 ZnO

Studies of Electron Trapping in ZnO Semiconductor 3  
*L. Chernyak, E. Flitsyan, M. Shatkhin and Z. Dashevsky*

Aluminum-Doped Zinc Oxide Thin Films for Opto-Electronic Applications 13  
*N. Hirahara, B. Onwona-Agyeman and M. Nakao*

Investigation and Fabrication of Bottom Gate ZnO:Al TFTs with Various Thicknesses  
of ZnO Buffer Layers 21  
*Y. Lin, H. Lee and C. Lee*

High Responsivity Ultraviolet Photodetector Based on p-GaN/i-ZnO Nanorod /n-ZnO:  
In Nanorod 27  
*C. Chen, J. Yan and C. Lee*

Epitaxial Growth of ZnO on LiAlO<sub>2</sub> and LiGaO<sub>2</sub> Substrates by Chemical Vapor  
Deposition 33  
*C. Chen, J. Yu, T. Huang, L. Chang and M. Chou*

### Chapter 2 III-Nitrides

Quasi-Ballistic Hole Transport in an AlGaN/GaN Nanowire 47  
*M. Mastro, H. Kim, J. Ahn, J. Kim, J. Hite and C. Eddy Jr.*

Light Extraction Enhancement of n-Side Up Light-Emitting Diodes Without Electrodes  
Covering by Wafer Bonding and Textured Surfaces 53  
*R. Horng, Y. Lu and D. Wu*

|  |    |
|--|----|
| AlGaIn/GaN HEMT Based Biosensor<br><i>S. Alur, T. Gnanaprakasa, Y. Wang, Y. Sharma, J. Dai, J. Hong, A. L. Simonian,<br/>M. Bozack, C. Ahyi and M. Park</i>                        | 61 |
| Development of Enhancement Mode AlN/Ultrathin AlGaIn/GaN HEMTs by Selective<br>Wet Etching<br><i>T. Anderson, M. Tadjer, M. Mastro, J. Hite, K. Hobart, C. Eddy Jr. and F. Kub</i> | 65 |
| ZnO Nanorod/p-GaN Heterostructured Light-Emitting Diodes Passivated Using<br>Photoelectrochemical Method<br><i>J. Yan and C. Lee</i>   | 71 |

### **Chapter 3 SiC and Related Materials**

|  |    |
|--|----|
| Etch Pits of 4H-Silicon Carbide Surface Formed Using Chlorine Trifluoride Gas<br><i>H. Habuka, K. Furukawa, K. Tanaka, Y. Katsumi, N. Takechi, K. Fukae and T. Kato</i>  | 81 |
| a-Plane GaN for Hydrogen Sensing Applications<br><i>K. Baik, W. Lim, S. Pearton, Y. Wang, F. Ren, J. Yang and S. Jang</i>  | 89 |
| Passivation of Deep Levels at the SiO <sub>2</sub> /SiC Interface<br><i>A. F. Basile, J. Rozen, X. Chen, S. Dhar, J. R. Williams, L. C. Feldman and<br/>P. M. Mooney</i> | 95 |

### **Chapter 4 General Poster Session**

|  |     |
|--|-----|
| <i>pnpn and npn</i> Heterostructural Optoelectronic Devices<br><i>D. Guo</i>   | 105 |
| <i>npn</i> Heterostructural Optoelectronic Switch with Collector Confinement Layer<br><i>D. Guo</i>  | 111 |
| Drain Leakage Current in MuGFETs at High Temperatures<br><i>J. Girollo Jr. and M. Bellodi</i>  | 119 |
| Fabrication of IGZO Sputtering Target and Its Applications to the Preparation of<br>Thin-Film Transistor Devices<br><i>C. C. Lo and T. Hsieh</i> | 131 |

|  |     |
|--|-----|
| Low-Resistivity and High-Transmittance Indium Gallium Zinc Oxide Films Prepared by Co-Sputtering $\text{In}_2\text{Ga}_2\text{ZnO}_7$ and $\text{In}_2\text{O}_3$ Targets<br><i>H. Chang, K. Huang, C. Chu, S. Chen, T. H. Huang and M. Wu</i> | 137 |
| InGaN-Based Light Emitting Diodes with an AlN Sacrificial Buffer Layer for Chemical Lift-Off Process<br><i>C. Lin, J. Dai and M. Lin</i>   | 149 |
| InGaN Light-Emitting Diode Structure on a Photoelectrochemical Treated GaN:Si Layer<br><i>K. Chen, C. Lin and C. Lin</i>   | 155 |
| Electron Paramagnetic Resonance Studies of Shallow Donors Behavior in Hydrogenated ZnO Films<br><i>L. Larina, N. Tsvetkov, J. Yang, K. Lim and O. Shevaleevskiy</i>  | 161 |
| $\text{Dy}^{3+}$ Emission from GaAlN Powder and Radio-Frequency Sputtered Thin Film<br><i>J. H. Tao, J. McKittrick, J. Talbot and K. C. Mishra</i>   | 169 |

## Chapter 5 Energy Devices

|  |     |
|--|-----|
| Cuprous Oxide Solution Preparation and Application to $\text{Cu}_2\text{O}$ -ZnO Solar Cells<br><i>A. Du Pasquier, Z. Duan, N. Pereira and Y. Lu</i> | 179 |
| Author Index   | 191 |